### 1. General description

NPN high-voltage low  $V_{CEsat}$  transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9540Z

### 2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified
- Medium power SMD plastic package

## 3. Applications

- LED driver for LED chain module
- LCD backlighting
- · Automotive motor management
- Switch Mode Power Supply (SMPS)

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	-	500	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	400	V
I <sub>C</sub>	collector current		-	-	1	А
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	100	155	-	



### 500 V, 1 A NPN high-voltage low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C; C
2	С	collector		В
3	E	emitter		
4	С	collector	∃1 ∃2 ∃3	Ė
			SC-73 (SOT223)	sym016

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	ber Package						
	Name	Description	Version				
PBHV8140Z		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223				

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBHV8140Z	V8140Z

#### 500 V, 1 A NPN high-voltage low VCEsat transistor

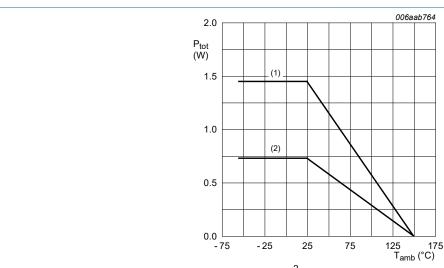
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	500	V
$V_{CEO}$	collector-emitter voltage	open base		-	400	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	500	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
Ic	collector current			-	1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	А
I <sub>BM</sub>	peak base current			-	400	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.45	W
			[2]	-	0.73	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

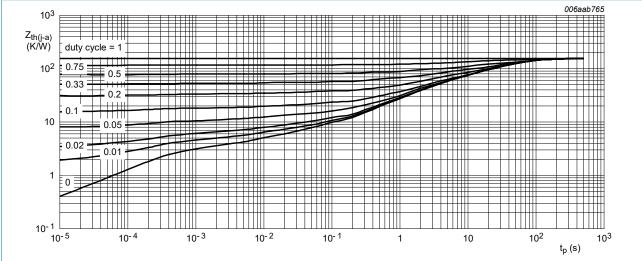
#### 500 V, 1 A NPN high-voltage low VCEsat transistor

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

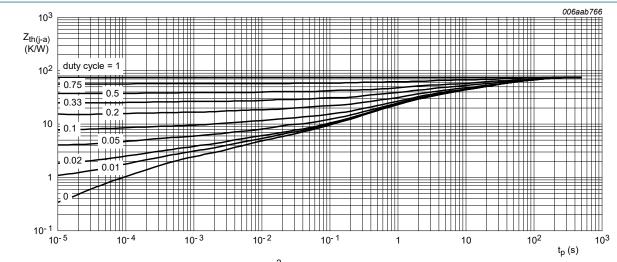
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	85	K/W
	junction to ambient		[2]	-	-	170	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 500 V, 1 A NPN high-voltage low VCEsat transistor

## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 320 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 320 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 320 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C	100	155	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; pulsed; $t_{p} \le$ 300 μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C	80	150	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; pulsed; $t_{p} \le$ 300 μs; $δ \le 0.02$ ; $T_{amb}$ = 25 °C	35	65	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	10	20	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 100 mA; $I_B$ = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	45	80	mV
		$I_{C}$ = 100 mA; $I_{B}$ = 20 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	30	50	mV
		$I_C$ = 500 mA; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	85	140	mV
		$I_C = 1 \text{ A}$ ; $I_B = 200 \text{ mA}$ ; pulsed; $t_p \le$	-	150	250	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	150	250	mΩ
$V_{BEsat}$	base-emitter saturation voltage		-	0.95	1.1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 6 V; I <sub>C</sub> = 0.5 A; I <sub>Bon</sub> = 0.1 A;	-	25	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	2820	-	ns
t <sub>on</sub>	turn-on time		-	2845	-	ns
t <sub>s</sub>	storage time		-	2585	-	ns
t <sub>f</sub>	fall time		-	1215	-	ns
t <sub>off</sub>	turn-off time		-	3800	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	-	25	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 20 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25  ^{\circ}\text{C}$	-	12	-	pF
C <sub>e</sub>	emitter capacitance	V <sub>EB</sub> = 0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	600	-	pF

#### 500 V, 1 A NPN high-voltage low VCEsat transistor

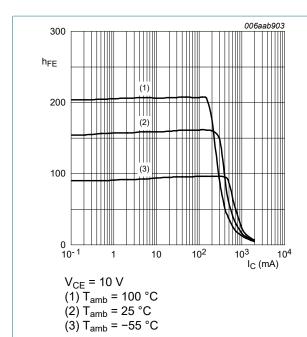


Fig. 4. DC current gain as a function of collector current; typical values

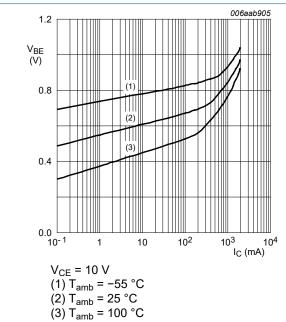


Fig. 6. Base-emitter voltage as a function of collector current; typical values

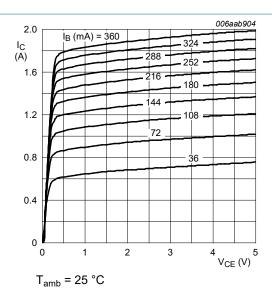
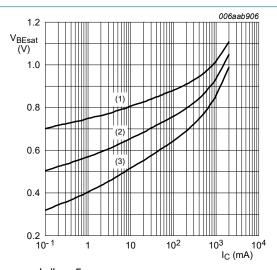


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_{C}/I_{B} = 5$  (1)  $T_{amb} = -55 \,^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

#### 500 V, 1 A NPN high-voltage low VCEsat transistor

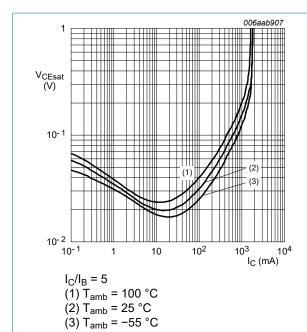


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

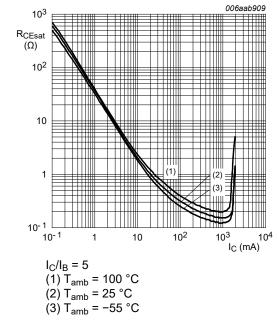


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

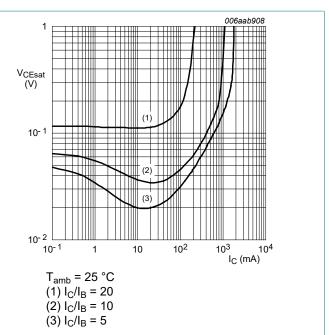


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

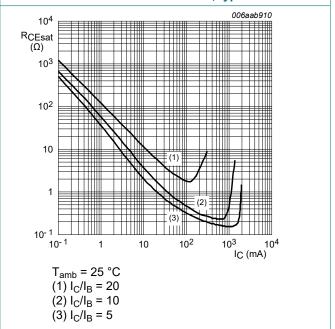
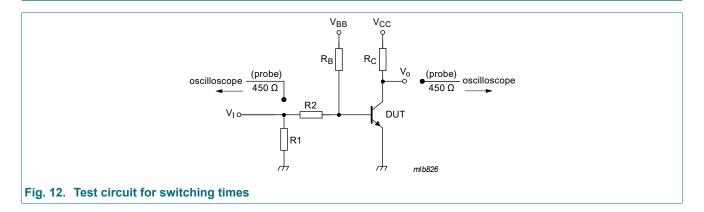


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

#### 500 V, 1 A NPN high-voltage low VCEsat transistor

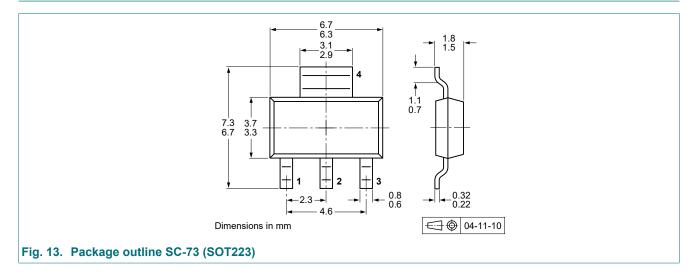
### 11. Test information



### **Quality information**

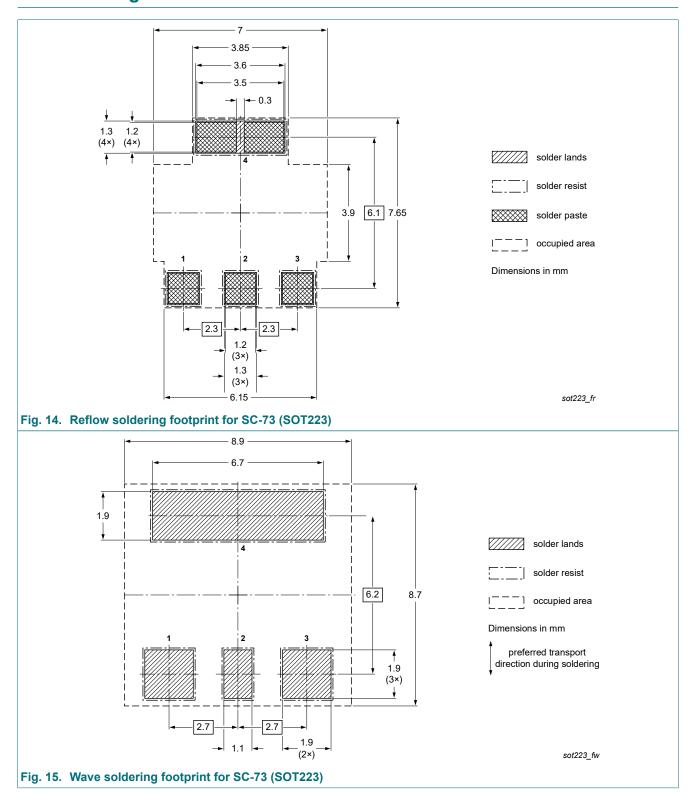
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline



### 500 V, 1 A NPN high-voltage low VCEsat transistor

## 13. Soldering



### 500 V, 1 A NPN high-voltage low VCEsat transistor

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBHV8140Z v.2	20230721	Product data sheet	-	PBHV8140Z_1			
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Section "Packing information" removed.</li> </ul>						
PBHV8140Z_1	20091211	Product data sheet	-	-			

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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### 500 V, 1 A NPN high-voltage low VCEsat transistor

## **Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10	. Characteristics	5
11.	Test information	8
12	Package outline	8
	Soldering	
	Revision history	
	Legal information	

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 21 July 2023

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